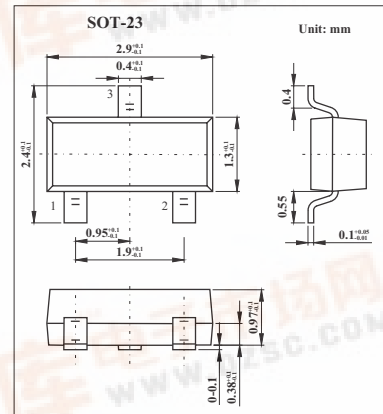


SMD Type Diodes

Silicon PIN Diode Array
BAR66

■ Features

- Surge protection device
- Two PIN diodes, series configuration
- Designed for surge overvoltage clamping in antiparallel connection



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse voltage	V _R	150	V
Forward current	I _F	200	mA
Forward current (tp = 1 μs)	I _F	20	A
Power dissipation, Ts ≤ 25°C ¹⁾	P _{tot}	250	mW
Operating temperature range	T _{op}	-55 to +150	°C
Storage temperature range	T _{stg}	-55 to +150	°C
Junction - ambient ¹⁾	R _{thJA}	≤ 450	K/W

Note

1. Package mounted on alumina 15mm × 16.7mm × 0.7mm

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse leakage	I _R	I _R = 5 μA	150			V
Forward voltage	V _F	I _F = 50 mA		0.95	1.2	V
Diode capacitance	C _T	V _R = 35 V, f = 1 MHz		0.4	0.6	pF
		V _R = 0, f = 100 MHz		0.35		
Forward resistance	r _f	I _F = 10 mA, f = 100 MHz		1.5		Ω
Charge carrier life time	τ _S	I _F = 10 mA, I _R = 6 mA, I _R = 3 mA		0.7		μs
Series inductance	L _s			2		nH

■ Marking

Marking	PMs
---------	-----

